NSN 5962-01-122-4541

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Maximum Power Dissipation Rating:
500.0 milliwatts
Operating Tempurature Range:
-0.0/+75.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Monolithic and programmable and 3-state output
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
10 input
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
-1.5 volts power source and 5.5 volts power source
Time Rating Per Chacteristic:
70.00 nanoseconds propagation delay time, low to high level output
Memory Device Type:
Rom
Test Data Document:
05869-726009-1 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
16 printed circuit
Shelf Life:
N/a
Unit Of Measure:

Demilitarization:
Yes - demil/mli
Fiig:
A458a0